L Number	Hits	Search Text	DB	Time stamp
1	337	(257/332).CCLS.	USPAT; US-PGPUB;	2004/07/16
			EPO; JPO; DERWENT	
2	79	((257/332).CCLS.) and breakdown adj voltage	USPAT; US-PGPUB; EPO; JPO;	2004/07/16
3	258	((257/332).CCLS.) not (((257/332).CCLS.) and breakdown adj voltage)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 09:54
5	208	(257/333).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:05
6	254	trench near (MOSFET DMOS) and breakdown adj voltage and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:40
7	46	(trench near (MOSFET DMOS) and breakdown adj voltage and epitaxial\$2) and deep adj body	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:05
8	10	6262453.URPN.	USPAT	2004/07/16
11	757	(VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16
12	10	((VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2) and (field adj relief gaurd	USPAT; US-PGPUB; EPO; JPO;	2004/07/16 10:48
13	7	adj ring) ((VDMOS trench near (gate MOSFET DMOS)) and breakdown adj voltage and epitaxial\$2) and buried adj region with body	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:49
14	184	(257/334).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 10:49
15	424	(257/331).CCLs.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16
16	584	(257/339).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16
18	100	(VDMOS trench near (gate MOSFET DMOS)) and ((257/339).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16
20	951	(257/330).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16
25	543	(257/302).CCLs.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/16 11:53
-	1	10/603461	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/13 12:54

_	2	10/437984	USPAT;	2004/07/13
	_		US-PGPUB;	13:09
			EPO; JPO;	
			DERWENT	
_	21	US-6090716-\$.DID. OR US-6069043-\$.DID. OR	USPAT;	2004/07/13
		US-5910669-\$.DID. OR US-5674766-\$.DID. OR	US-PGPUB;	13:56
	ļ	US-5665996-\$.DID. OR US-5592005-\$.DID. OR	EPO; JPO;	
		US-5298442-\$.DID. OR US-5072266-\$.DID. OR	DERWENT	
		US-5034785-\$.DID. OR US-4967245-\$.DID. OR		1
		US-4767722-\$.DID.		
_	13	(timothy near3 henson).in.	USPAT;	2004/07/13
		(US-PGPUB;	14:06
			EPO; JPO;	11100
			DERWENT	
_	587	(257/329).CCLS.	USPAT;	2004/07/14
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	15:26
			EPO; JPO;	13.20
			DERWENT	
_	376	((257/329).CCLS.) not (((257/331).CCLS.)	USPAT;	2004/07/14
	3,0	((257/330).CCLS.))	US-PGPUB;	15:27
		((23,7,330).0013.77	EPO; JPO;	13.27
			DERWENT	
_	149	(((257/329).CCLS.) not (((257/331).CCLS.)	USPAT;	2004/07/14
	143	((257/323).CCLS.))) and trench	US-PGPUB;	15:27
		((237/330):CCHS:/// and Clench	EPO; JPO;	15.27
			DERWENT	
_	4	(((257/330).CCLS.) ((257/331).CCLS.)	USPAT;	2004/07/14
	· ·	((257/329).CCLS.) ((257/332).CCLS.)	US-PGPUB;	15:29
		((257/333).CCLS.)) and field adj relief	EPO; JPO;	13.29
		((237/333).ccbs./) and field adj feller	DERWENT	į į
_	47	trench near (MOSFET DMOS) and breakdown	USPAT;	2004/07/14
	1 1	adj voltage and deep adj body	US-PGPUB;	15:51
		adj vortage and deep adj body	EPO; JPO;	15:51
			DERWENT	
_	1	(trench near (MOSFET DMOS) and breakdown	USPAT;	2004/07/14
	<u> </u>	adj voltage and deep adj body) not	USPAT; US-PGPUB;	15:51
		((trench near (MOSFET DMOS) and breakdown	- · · - ·	15:51
		adj voltage and epitaxial\$2) and deep adj	EPO; JPO; DERWENT	
		adj voitage and epitaxiai\$2) and deep adj body)	DEKWENT	
_	2		HCD2m.	2004/07/14
-			USPAT;	2004/07/14
		adj voltage and buried adj body	US-PGPUB;	15:51
			EPO; JPO;	